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Substitute for form 1449/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (as many sheets as necessary)	Complete if Known	
	Application Number	10/721920
	Filing Date	November 24, 2003
	First Named Inventor	Ahn, Kie
	Group Art Unit	2822
	Examiner Name	Trinh, Michael
Sheet 1 of 4		Attorney Docket No: 303.685US2

US PATENT DOCUMENTS						
Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate

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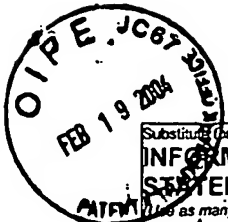
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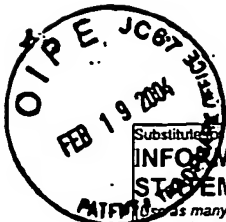
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Substitute Disclosure Statement Form (PTO-1448)

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 608. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. Applicant's unique citation designation number (optional). Applicant is to place a check mark here if English language Translation is attached



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	Application Number	10/721920
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	First Named Inventor	Ahn, Kie
	Group Art Unit	2822
	Examiner Name	Trinh, Michael
Sheet 3 of 4	Attorney Docket No: 303.685US2	

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

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Substitute for form 1449A/PTO.

INFORMATION DISCLOSURE
STATEMENT BY APPLICANT

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First Named Inventor	Ahn, Kie
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Sheet 4 of 4

Attorney Docket No: 303.685US2

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

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EXAMINER

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Substitute Disclosure Statement Form (PTO-1449)

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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)	Complete if Known	
	Applicant Number	Unknown 10/721920
	Filing Date	Even Date Herewith
	First Named Inventor	Ahn, Kie
	Group Art Unit	Unknown 2822
	Examiner Name	Unknown
Sheet 1 of 9	Attorney Docket No: 303.685US2	

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	First Named Inventor	Ahn, Kie
	Group Art Unit	Unknown
	Examiner Name	Unknown
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Application Number	Unknown 10/721920
Filing Date	Even Date Herewith
First Named Inventor	Ahn, Kie
Group Art Unit	Unknown
Examiner Name	Unknown

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	Applicant Number	Unknown 10/721920
	Filing Date	Even Date Herewith
	First Named Inventor	Ahn, Kie
	Group Art Unit	Unknown
	Examiner Name	Unknown
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Applicant Number	Unknown 10/721920
Filing Date	Even Date Herewith
First Named Inventor	Ahn, Kie
Group Art Unit	Unknown
Examiner Name	Unknown

Sheet 6 of 9

Attorney Docket No: 303.685US2

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	First Named Inventor	Ahn, Kie
	Group Art Unit	Unknown
	Examiner Name	Unknown
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Applicant Number	Unknown- 10/721920
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First Named Inventor	Ahn, Kie
Group Art Unit	Unknown
Examiner Name	Unknown

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	Application Number	Unknown — 10/721920
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	First Named Inventor	Ahn, Kie
	Group Art Unit	Unknown
	Examiner Name	Unknown
Sheet 9 of 9	Attorney Docket No: 303.685US2	

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EXAMINER	Michael Trib.	DATE CONSIDERED	12/12/04
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Substitute Disclosure Statement Form (PTO-1449)
 * EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 809. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. Applicant's unique citation designation number (optional) ? Applicant is to place a check mark here if English language Translation is attached